

## **ISC Silicon NPN Power Transistor**

2SC3421

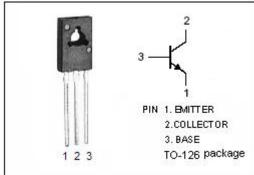
#### **DESCRIPTION**

- High Collector-Emitter Breakdown Voltage
  - : V<sub>(BR)CEO</sub>= 120V(Min)
- · Complement to Type 2SA1358
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



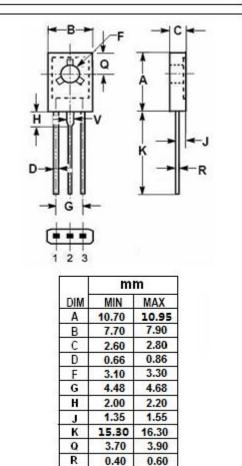
### **APPLICATIONS**

- Designed for audio frequency power amplifier applications.
- Suitable for driver of 60 to 80 Watts audio amplifier.



# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	120	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	120	V	
$V_{EBO}$	Emitter-Base Voltage 5		V	
Ic	Collector Current-Continuous 1		А	
I <sub>B</sub>	Base Current-Continuous	0.1	А	
Pc	Collector Power Dissipation @ T <sub>C</sub> =25 °C	10	W	
	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.5		
TJ	Junction Temperature	150	$^{\circ}$	
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$ C	



1.17



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### **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	120			V		
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA ; I <sub>C</sub> = 0	5			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 500mA; I <sub>B</sub> = 50mA			1.0	V		
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 500mA ; V <sub>CE</sub> = 5V			1.0	V		
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			0.1	μА		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	μА		
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	80		240			
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V		120		MHz		
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V, f <sub>test</sub> = 1MHz		15		pF		

### ♦ h<sub>FE</sub> Classifications

0	Y		
80-160	120-240		

### NOTICE:

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